



BC847BVN

COMPLEMENTARY PAIR SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Die Construction**
- Two Internally Isolated NPN/PNP Transistors in One Package
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- **PPAP** Capable (Note 4)

Mechanical Data

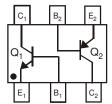
- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.003 grams (Approximate)



Top View



Bottom View



Device Schematic Top View

Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC847BVN-7	AEC-Q101	KAW	7	8	3,000
BC847BVNQ-7	Automotive	KAW	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

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2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

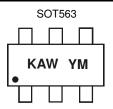
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



KAW = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011)M = Month (ex: 9 = September)

Date Code Ke	ey .											
Year	2010	201	1	2012	20	013	2014	2	2015	2016		2017
Code	Х	Y		Z		A	В		С	D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings: NPN, BC847B Type (Q₁) (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	Ι _C	100	mA
Peak Collector Current	ICM	200	mA
Peak Emitter Current	I _{EM}	200	mA

Maximum Ratings: PNP, BC857B Type (Q₂) (@T_A = +25 °C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current	lc	-100	mA
Peak Collector Current	ICM	-200	mA
Peak Emitter Current	I _{EM}	-200	mA

Thermal Characteristics – Total Device (@T_A = +25 °C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Total Device	PD	150	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	833	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-65 to +150	C

Note: 6. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

Electrical Characteristics: NPN, BC847B Type (Q1) (@TA = +25 °C unless otherwise specified.)

Characteristic (Note 7)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	-	—	V	$I_{\rm C} = 100 \mu {\rm A}, I_{\rm B} = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	45		—	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	$I_E = 100 \mu A, I_C = 0$
DC Current Gain	h _{FE}	200	290	450	_	$V_{CE} = 5.0V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	90 200	250 600	mV	$I_{C} = 10mA, I_{B} = 0.5mA$ $I_{C} = 100mA, I_{B} = 5.0mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	700 900	—	mV	$I_{C} = 10mA, I_{B} = 0.5mA$ $I_{C} = 100mA, I_{B} = 5.0mA$
Base-Emitter Voltage	V _{BE(on)}	580 —	660 —	700 720	mV	$V_{CE} = 5.0V, I_{C} = 2.0mA$ $V_{CE} = 5.0V, I_{C} = 10mA$
Collector-Cutoff Current	I _{CBO}	_		15 5.0	nA μA	V _{CB} = 30V V _{CB} = 30V, T _A = +150℃
Gain Bandwidth Product	fT	100	300	—	MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz
Collector-Base Capacitance	Ссво	_	3.5	6.0	pF	V _{CB} = 10V, f = 1.0MHz

Note: 7. Short duration pulse test used to minimize self-heating effect.



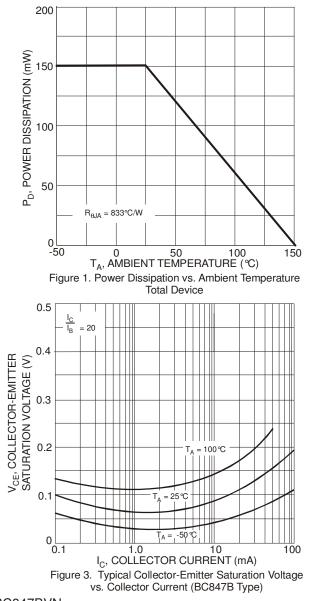
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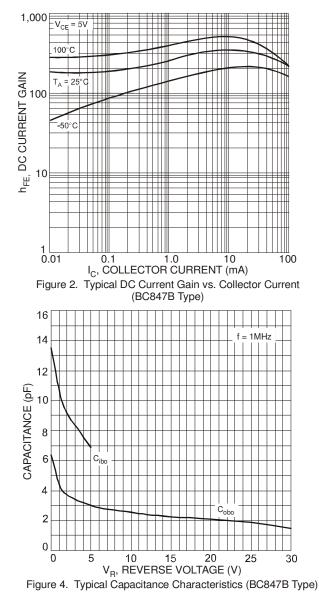
Electrical Characteristics: PNP, BC857B Type (Q₂) (@T_A = +25 °C unless otherwise specified.)

Characteristic (Note 8)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	—	—	V	$I_{\rm C} = -100 \mu A, I_{\rm B} = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-45	—	—	V	$I_{C} = -10mA, I_{B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	_	—	V	$I_E = -100 \mu A$, $I_C = 0$
DC Current Gain	h _{FE}	220	290	475	_	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	-75 -250	-300 -650	mV	$\label{eq:IC} \begin{array}{l} I_C = -10mA, \ I_B = -0.5mA \\ I_C = -100mA, \ I_B = -5.0mA \end{array}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	-700 -850	 -950	mV	$I_{C} = -10mA$, $I_{B} = -0.5mA$ $I_{C} = -100mA$, $I_{B} = -5.0mA$
Base-Emitter Voltage	V _{BE(on)}	-600	-650 —	-750 -820	mV	$V_{CE} = -5.0V, I_{C} = -2.0mA$ $V_{CE} = -5.0V, I_{C} = -10mA$
Collector-Cutoff Current	I _{CBO}	_	—	-15	nA	V _{CB} = -30V
	-CBO	_	—	-4.0	μΑ	V _{CB} = -30V, T _A = +150 ℃
Gain Bandwidth Product	fT	100	200	—	MHz	V _{CE} = -5.0V, I _C = -10mA, f = 100MHz
Collector-Base Capacitance	C _{CBO}	_	3	4.5	pF	V _{CB} = -10V, f = 1.0MHz

Note: 8. Short duration pulse test used to minimize self-heating effect.

Thermal Characteristics – Total Device

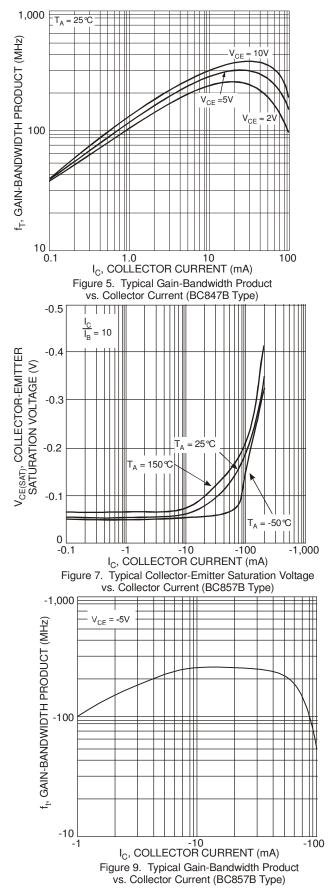


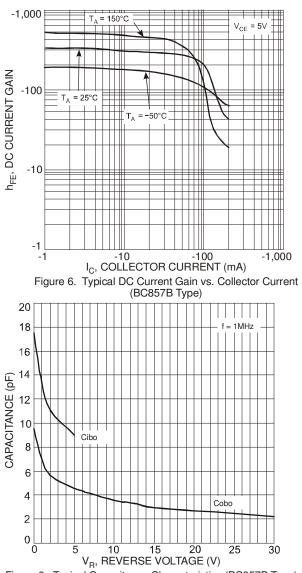


BC847BVN Document number: DS30627 Rev. 7 - 2 Downloaded from Arrow.com.



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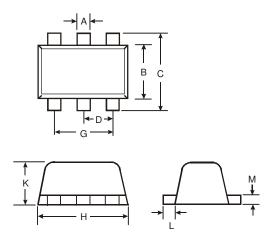






Package Outline Dimensions

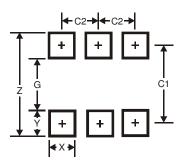
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
Κ	0.55	0.60	0.60				
L	0.10	0.30	0.20				
М	0.10	0.18	0.11				
All	Dimens	sions in	mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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